

# N-channel TrenchMOS standard level FET Rev. 02 — 27 January 2011

Product data sheet

#### **Product profile** 1.

#### 1.1 General description

Standard level N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using TrenchMOS technology. This product has been designed and qualified to the appropriate AEC standard for use in automotive critical applications.

#### 1.2 Features and benefits

- AEC Q101 compliant
- Low conduction losses due to low on-state resistance

### **1.3 Applications**

- 12 V and 24 V loads
- Automotive and general purpose power switching

### 1.4 Quick reference data

#### Suitable for standard level gate drive sources

- Suitable for thermally demanding environments due to 175 °C rating
- Motors, lamps and solenoids

Table 1.	Quick reference data						
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C		-	-	55	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = 10 V; T <sub>mb</sub> = 25 °C; see <u>Figure 3</u> ; see <u>Figure 1</u>	<u>[1]</u>	-	-	62	A
P <sub>tot</sub>	total power dissipation	$T_{mb} = 25 \text{ °C}; \text{ see } \frac{\text{Figure 2}}{\text{Figure 2}}$		-	-	115	W
Static cha	aracteristics						
R <sub>DSon</sub>	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A};$ $T_j = 25 \text{ °C}; \text{see } Figure 11;$ see Figure 12		-	13	15	mΩ



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Table 1.	Quick reference data	continued				
Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
Avalanch	e Ruggedness					
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	$ \begin{split} &I_D = 62 \text{ A};  \text{V}_{\text{sup}} \leq 55 \text{ V}; \\ &R_{\text{GS}} = 50  \Omega;  \text{V}_{\text{GS}} = 10 \text{ V}; \\ &T_{\text{j(init)}} = 25 ^{\circ}\text{C}; \text{ unclamped} \end{split} $	-	-	211	mJ
Dynamic	characteristics					
Q <sub>GD</sub>	gate-drain charge	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; V <sub>DS</sub> = 44 V; T <sub>j</sub> = 25 °C; see <u>Figure 13</u>	-	19	-	nC

SOT428 (DPAK)

[1] Current is limited by power dissipation chip rating.

### 2. Pinning information

Table 2.	Pinning	j information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		5
2	D	drain	mb	
3	S	source		
mb	D	mounting base; connected to drain		mbb076 S

# 3. Ordering information

Table 3. Ordering	g information		
Type number	Package		
	Name	Description	Version
BUK7215-55A	DPAK	plastic single-ended surface-mounted package (DPAK); 3 leads (one lead cropped)	SOT428

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### 4. Limiting values

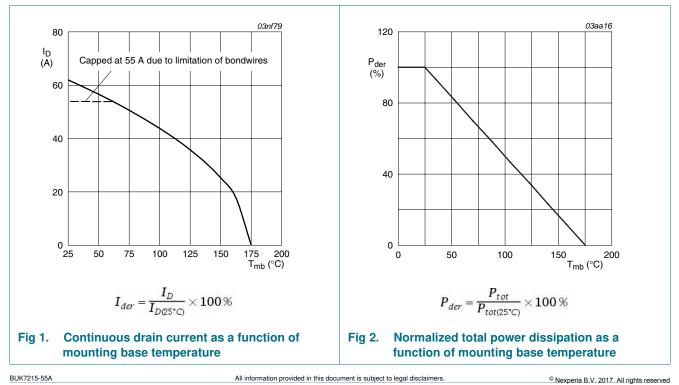
#### Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

		0, (,				
Symbol	Parameter	Conditions		Min	Мах	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C		-	55	V
V <sub>DGR</sub>	drain-gate voltage	$R_{GS} = 20 \text{ k}\Omega$		-	55	V
V <sub>GS</sub>	gate-source voltage			-20	20	V
I <sub>D</sub>	drain current	$T_{mb}$ = 100 °C; $V_{GS}$ = 10 V; see <u>Figure 1</u>	[1]	-	44	А
		$T_{mb} = 25 \text{ °C}; V_{GS} = 10 \text{ V}; \text{ see } Figure 3;$	<u>[1]</u>	-	62	А
		see <u>Figure 1</u>	[2]	-	55	А
I <sub>DM</sub>	peak drain current	T <sub>mb</sub> = 25 °C; pulsed; t <sub>p</sub> ≤ 10 μs; see <u>Figure 3</u>		-	248	A
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; see <u>Figure 2</u>		-	115	W
T <sub>stg</sub>	storage temperature			-55	175	°C
Tj	junction temperature			-55	175	°C
Source-drai	in diode					
I <sub>S</sub>	source current	T <sub>mb</sub> = 25 °C	[1]	-	62	А
			[2]	-	55	А
I <sub>SM</sub>	peak source current	pulsed; $t_p \le 10 \ \mu s$ ; $T_{mb} = 25 \ ^{\circ}C$		-	248	А
Avalanche I	Ruggedness					
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	I <sub>D</sub> = 62 A; V <sub>sup</sub> ≤ 55 V; R <sub>GS</sub> = 50 Ω; V <sub>GS</sub> = 10 V; T <sub>j(init)</sub> = 25 °C; unclamped		-	211	mJ

[1] Current is limited by power dissipation chip rating.

[2] Continuous current is limited by bond wires.



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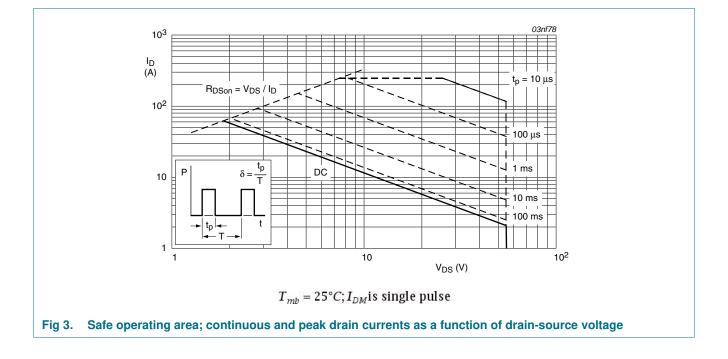


Table 5

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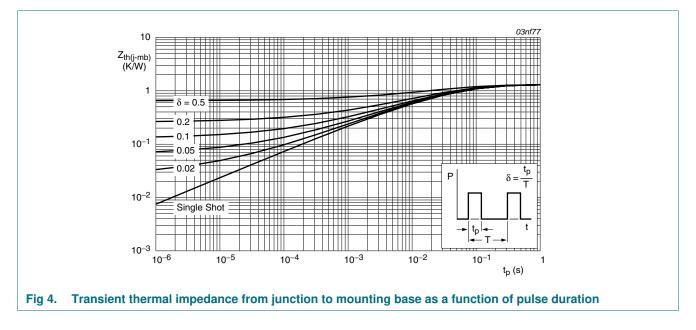
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### 5. Thermal characteristics

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Table 5.	Inermal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	see Figure 4	-	-	1.3	K/W
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	minimum footprint ; FR4 printed circuit board	-	71.4	-	K/W

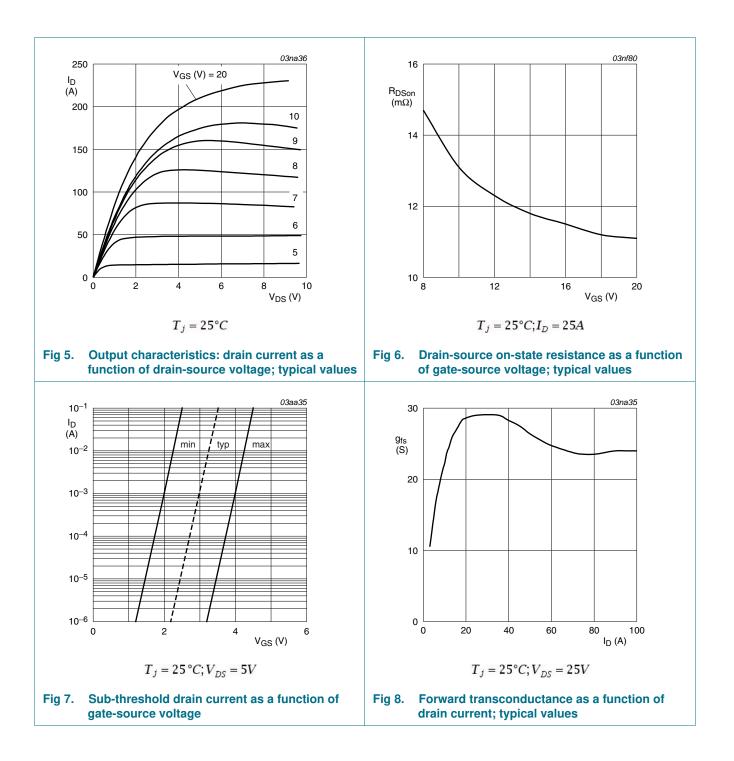


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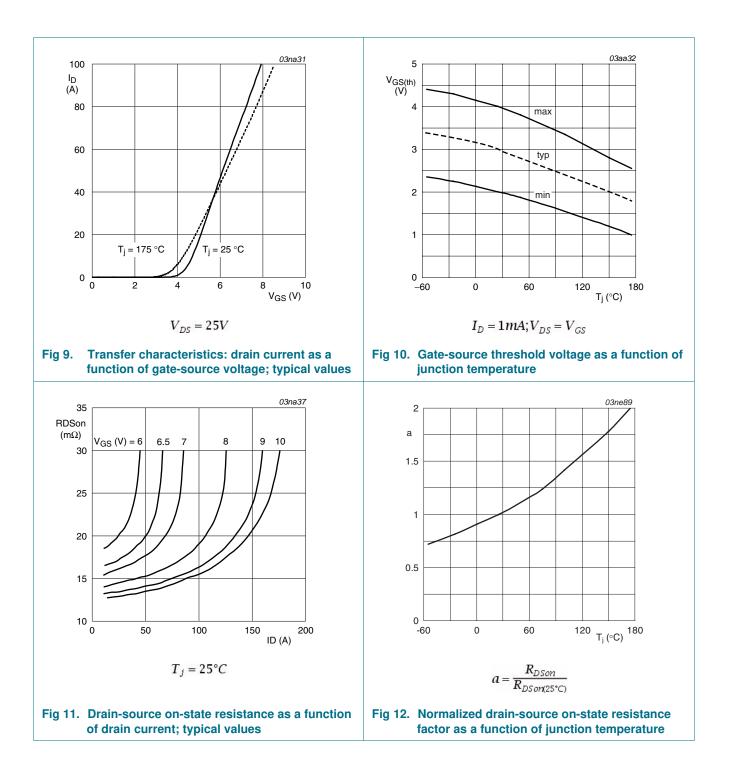
### 6. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics					
V <sub>(BR)DSS</sub>	drain-source breakdown	I <sub>D</sub> = 0.25 mA; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C	55	-	-	V
( )	voltage	I <sub>D</sub> = 0.25 mA; V <sub>GS</sub> = 0 V; T <sub>i</sub> = -55 °C	50	-	-	V
V <sub>GS(th)</sub>	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C};$ see Figure 10	2	3	4	V
		$I_D = 1 \text{ mA; } V_{DS} = V_{GS}; T_j = 175 \text{ °C};$ see Figure 10	1	-	-	V
	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C};$ see <u>Figure 10</u>		-	-	4.4	V
I <sub>DSS</sub>	drain leakage current	$V_{DS} = 55 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 175 \text{ °C}$	-	-	500	μA
		$V_{DS} = 55 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	0.05	10	μA
I <sub>GSS</sub>	gate leakage current	$V_{GS} = 20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	2	100	nA
		$V_{GS}$ = -20 V; $V_{DS}$ = 0 V; $T_j$ = 25 °C	-	2	100	nA
R <sub>DSon</sub>	drain-source on-state resistance	$V_{GS}$ = 10 V; $I_D$ = 25 A; $T_j$ = 175 °C; see <u>Figure 11</u> ; see <u>Figure 12</u>	-	-	30	mΩ
		$V_{GS}$ = 10 V; $I_D$ = 25 A; $T_j$ = 25 °C; see Figure 11; see Figure 12	-	13	15	mΩ
Dynamic ch	aracteristics					
Q <sub>G(tot)</sub>	total gate charge	$I_D = 25 \text{ A}; V_{DS} = 44 \text{ V}; V_{GS} = 10 \text{ V};$	-	50	-	nC
Q <sub>GS</sub>	gate-source charge	T <sub>j</sub> = 25 °C; see <u>Figure 13</u>	-	9	-	nC
Q <sub>GD</sub>	gate-drain charge		-	19	-	nC
C <sub>iss</sub>	input capacitance	$V_{GS} = 0 V; V_{DS} = 25 V; f = 1 MHz;$	-	1580	2107	pF
C <sub>oss</sub>	output capacitance	$T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure } 14}{14}$	-	370	446	pF
C <sub>rss</sub>	reverse transfer capacitance		-	220	300	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS} = 30 \text{ V}; \text{ R}_{L} = 1.2 \Omega; \text{ V}_{GS} = 10 \text{ V};$	-	26	-	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 10 \ \Omega; T_j = 25 \ ^{\circ}C$	-	99	-	ns
t <sub>d(off)</sub>	turn-off delay time		-	73	-	ns
t <sub>f</sub>	fall time		-	65	-	ns
L <sub>D</sub>	internal drain inductance	measured from drain to centre of die ; $T_j = 25 \ ^\circ C$	-	2.5	-	nH
L <sub>S</sub>	internal source inductance	measured from source to source bond pad ; $T_j = 25 \text{ °C}$	-	7.5	-	nH
Source-drai	in diode					
V <sub>SD</sub>	source-drain voltage	I <sub>S</sub> = 25 A; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C; see <u>Figure 15</u>	-	0.85	1.2	V
t <sub>rr</sub>	reverse recovery time	$I_{S} = 25 \text{ A}; \text{ d}I_{S}/\text{d}t = -100 \text{ A}/\mu\text{s};$	-	48	-	ns
Q <sub>r</sub>	recovered charge	$V_{GS}$ = -10 V; $V_{DS}$ = 30 V; $T_j$ = 25 °C	-	106	-	nC

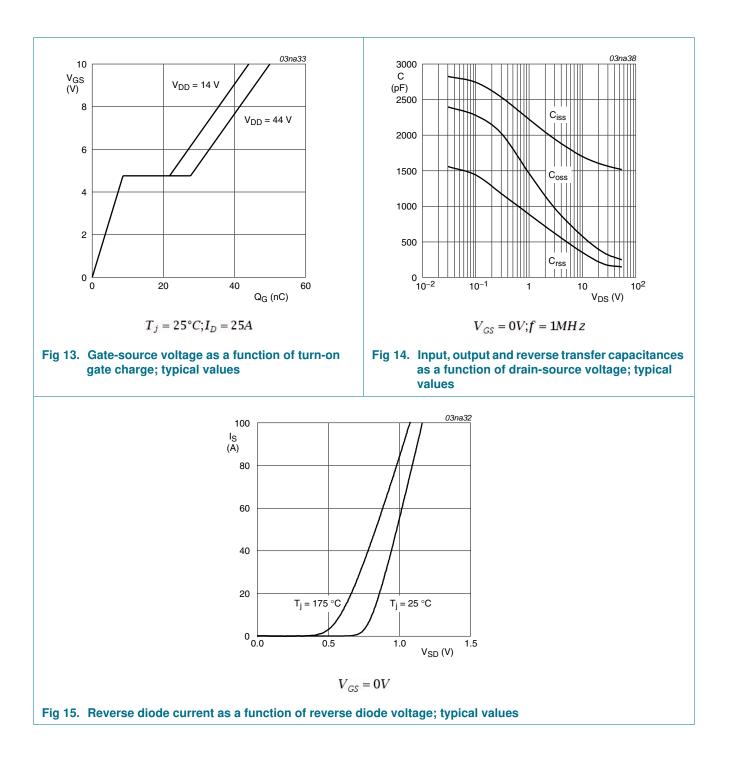
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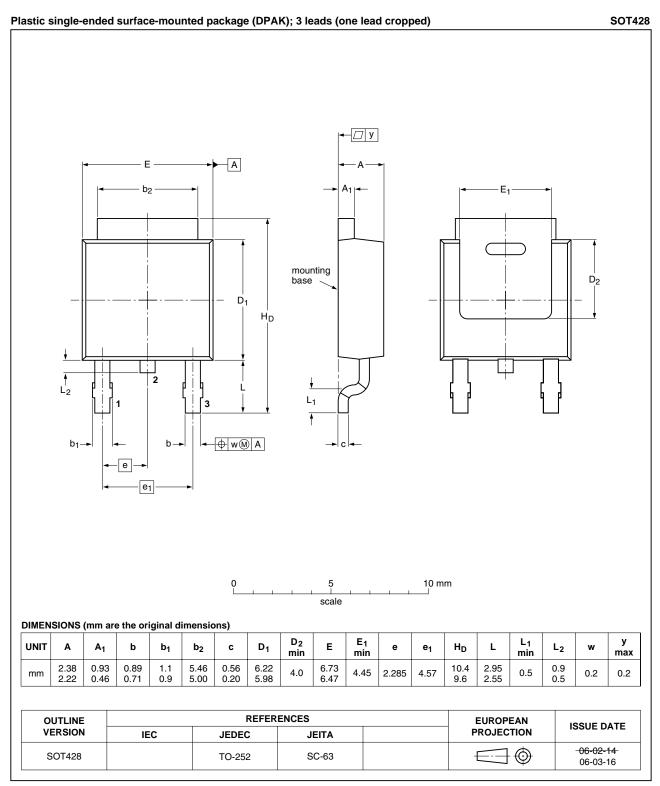


# BUK7215-55A



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### 7. Package outline



#### Fig 16. Package outline SOT428 (DPAK)

BUK7215-55A Product data sheet

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# 8. Revision history

Table 7. Revision	history			
Document ID	Release date	Data sheet status	Change notice	Supersedes
BUK7215-55A v.2	20110127	Product data sheet	-	BUK7215_55A v.1
Modifications:	<ul> <li>The format of of NXP Semic</li> </ul>	this data sheet has been rec conductors.	designed to comply with	n the new identity guidelines
	<ul> <li>Legal texts had</li> </ul>	we been adapted to the new	company name where	appropriate.
BUK7215_55A v.1	20010816	Product data	-	-

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#### 9.1 Data sheet status

Document status[1][2]	Product status <sup>[3]</sup>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL <u>http://www.nexperia.com</u>.

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